

semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula $\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$, and $x+y+z=1$, wherein the full width at half maximum of the (0004) reflection X-ray rocking curve of said second III-V compound semiconductor is 700 seconds or less regardless of the direction of X-ray incidence, and the compound semiconductor is formed by a vapor phase epitaxy method.

2. (Twice Amended) A III-V compound semiconductor having a first layer that comprises a first III-V compound semiconductor expressed by the general formula $\text{In}_u\text{Ga}_v\text{Al}_w\text{N}$ where $0 \leq u \leq 1$, $0 \leq v \leq 1$, $0 \leq w \leq 1$, and $u+v+w=1$, a pattern on said first layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula $\text{In}_x\text{Ga}_y\text{Al}_z\text{N}$ where $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$, and $x + y + z = 1$, wherein an upper surface of said pattern is not in contact with said second III-V compound semiconductor, and the compound semiconductor is formed by a vapor phase epitaxy method.